

| | Type | L # | Hits | Search Text | DBs | Time Stamp |
|---|------|-----|-------------|-------------------------------|--|---------------------|
| 1 | BRS | L1 | 62031 | "thin film transistor" or TFT | USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B | 2004/06/17 17:33 |
| 2 | BRS | L2 | 868856 | gate | USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B | 2004/06/17 17:33 |
| 3 | BRS | L3 | 178467 5 | substrate | USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B | 2004/06/17 17:33 |
| 4 | BRS | L4 | 421191 | impurity or impurities | USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B | 2004/06/17 17:33 |
| 5 | BRS | L5 | 274141 | implant\$6 or inplant\$6 | USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B | 2004/06/17 17:33 |

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| 6 | BRS | L6 | 558585 | diffus\$6 | USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B | 2004/06/17 17:33 |
| 7 | BRS | L7 | 55932 | asi or a-si or "amorphous silicon" | USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B | 2004/06/17 17:33 |
| 8 | BRS | L8 | 628490 9 | resistance or R | USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B | 2004/06/17 17:33 |
| 9 | BRS | L9 | 2285 | ((impurity or impurities) near4 (asi or a-si or "amorphous silicon")) | USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B | 2004/06/17 17:33 |
| 10 | BRS | L10 | 951 | ((impurity or impurities) near4 (asi or a-si or "amorphous silicon")) same gate | USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B | 2004/06/17 17:33 |

| | Type | L # | Hits | S arch Text | DBs | Tim Stamp |
|----|------|-----|------|---|--|---------------------|
| 11 | BRS | L11 | 528 | ((impurity or impurities) near4 (asi or a-si or "amorphous silicon")) same gate) same substrate | USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B | 2004/06/17 17:34 |
| 12 | BRS | L13 | 403 | (asi or a-si or "amorphous silicon") near8 gate near8 (impurity or impurities) | USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B | 2004/06/17 17:34 |
| 13 | BRS | L14 | 30 | ((asi or a-si or "amorphous silicon") near8 gate near8 (impurity or impurities)) near8 surface | USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B | 2004/06/17 17:34 |
| 14 | BRS | L16 | 5829 | (remov\$4 or etch\$6) near8 (asi or a-si or "amorphous silicon") | USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B | 2004/06/17 17:34 |
| 15 | BRS | L17 | 1471 | ((remov\$4 or etch\$6) near8 (asi or a-si or "amorphous silicon")) same source same drain | USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B | 2004/06/17 17:34 |

| | Type | L # | Hits | S arch Text | DBs | Tim Stamp |
|----|------|-----|-------------|---|--|---------------------|
| 16 | BRS | L18 | 979 | ((remov\$4 or etch\$6) near8 (asi or a-si or "amorphous silicon")) same source same drain) same gate | USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B | 2004/06/17 17:35 |
| 17 | BRS | L19 | 756 | ((remov\$4 or etch\$6) near8 (asi or a-si or "amorphous silicon")) same source same drain) same gate) and ("thin film transistor" or TFT) | USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B | 2004/06/17 17:35 |
| 18 | BRS | L21 | 122 | ((remov\$4 or etch\$6) near8 (asi or a-si or "amorphous silicon")) same source same drain) same gate) same "channel region" | USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B | 2004/06/17 17:35 |
| 19 | BRS | L23 | 968 | ((remov\$4 or etch\$6) near8 (asi or a-si or "amorphous silicon")) near8 (contact or channel) | USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B | 2004/06/17 17:36 |
| 20 | BRS | L25 | 543380 2 | diffus\$6 or dop\$6 or push\$6 or dispers\$6 or scatter\$6 or distribut\$6 or forc\$4 or emerg\$4 | USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B | 2004/06/17 17:36 |

| | Type | L # | Hits | Search T xt | DBs | Tim Stamp |
|----|------|-----|-------|---|--|---------------------|
| 21 | BRS | L26 | 13259 | (diffus\$6 or dop\$6 or push\$6 or dispers\$6 or scatter\$6 or distribut\$6 or forc\$4 or emerg\$4) near4 (phosphorus or P or impurity or impurities) near8 contact | USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B | 2004/06/17 17:37 |
| 22 | BRS | L27 | 577 | ((diffus\$6 or dop\$6 or push\$6 or dispers\$6 or scatter\$6 or distribut\$6 or forc\$4 or emerg\$4) near4 (phosphorus or P or impurity or impurities) near8 contact) same (asi or a-si or "amorphous silicon") | USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B | 2004/06/17 17:37 |
| 23 | BRS | L12 | 73 | (((((impurity or impurities) near4 (asi or a-si or "amorphous silicon"))) same gate) same substrate) same (implant\$6 or inplant\$6) | USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B | 2004/06/17 17:38 |
| 24 | BRS | L15 | 17 | ((asi or a-si or "amorphous silicon") near8 gate near8 (impurity or impurities) near8 surface) and ("thin film transistor" or TFT) | USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B | 2004/06/17 17:38 |
| 25 | BRS | L20 | 540 | (((((remov\$4 or etch\$6) near8 (asi or a-si or "amorphous silicon"))) same source same drain) same gate) and ("thin film transistor" or TFT)) and (@ad<20010219) | USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B | 2004/06/17 17:38 |

| | Type | L # | Hits | Search T xt | DBs | Tim Stamp |
|----|------|-----|------|--|--|---------------------|
| 26 | BRS | L22 | 104 | (((((remov\$4 or etch\$6) near8 (asi or a-si or "amorphous silicon"))) same source same drain) same gate) same "channel region") and ("thin film transistor" or TFT) | USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B | 2004/06/17 17:38 |
| 27 | BRS | L24 | 21 | ((remov\$4 or etch\$6) near8 (asi or a-si or "amorphous silicon"))) near8 (contact or channel)) near16 (resistance or R) | USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B | 2004/06/17 17:38 |
| 28 | BRS | L28 | 389 | ((((diffus\$6 or dop\$6 or push\$6 or dispers\$6 or scatter\$6 or distribut\$6 or forc\$4 or emerg\$4) near4 (phosphorus or P or impurity or impurties) near8 contact) same (asi or a-si or "amorphous silicon"))) and ("thin film transistor" or TFT) | USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B | 2004/06/17 17:38 |
| 29 | BRS | L29 | 217 | ((((diffus\$6 or dop\$6 or push\$6 or dispers\$6 or scatter\$6 or distribut\$6 or forc\$4 or emerg\$4) near4 (phosphorus or P or impurity or impurties) near8 contact) same (asi or a-si or "amorphous silicon"))) and ("thin film transistor" or TFT)) and (@ad<20010219) | USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B | 2004/06/17 17:38 |
| 30 | BRS | L30 | 32 | diffus\$6 near4 (phosphorus or P or phosphorous) near4 "contact portion" | USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B | 2004/06/17 17:43 |

| | Type | L # | Hits | S arch T xt | DBs | Tim Stamp |
|----|------|-----|-------|--|--|---------------------|
| 31 | BRS | L32 | 6303 | (impurity or impurities or Phosphorous or P or phosphorus) near4 7 | USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B | 2004/06/17 17:43 |
| 32 | BRS | L33 | 67286 | diffus\$6 near4 (phosphorus or P or phosphorous or impurity or impurities) | USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B | 2004/06/17 17:43 |
| 33 | BRS | L34 | 1140 | 32 and 33 | USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B | 2004/06/17 17:43 |
| 34 | BRS | L35 | 390 | 34 and 1 | USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B | 2004/06/17 18:07 |
| 35 | BRS | L36 | 268 | 35 and (@ad<20010219) | USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B | 2004/06/17 18:07 |